Table 1

	Etching Time (sec.) Other Forming Condition	Surface Shape of Second Transparent Conductive Layer				I_{220}/I_{111} *
		Hole Diameter (nm)	Hole Depth (nm)	Irregularity Size on Hole (nm)	Irregularity Size on other than Hole (nm)	
Ex 1	180	200-1400	80 – 1000	10 – 280 Average 120	<10	3
Ex 2	240	400-1000	100 – 700	20 – 200 Average 150	20 – 40	3
Ex 3	240	400-1000	100 – 700	20 – 200 Average 150	20 – 40	5.5
Ex 4	180 ZnO / ZnO	200-1400	80 – 1000	20 – 280 Average 130	20 – 50	3
Ex 5	--	400-1000	100 – 700	30 – 120 Average 80	30 –120	3
Co Ex 1	ZnO /SnO_2	--	--	--	Average 150	1.5
Co Ex 2	60	50-200	10 – 100	<10	<10	3
Co Ex 3	--	800-3000	700-2000	150 – 500 Average 350	150 – 500	1.4

* : Orientation of crystalline silicon photoelectric conversion layer

A1

Please replace the paragraph beginning at page 32, line 7, with the following rewritten paragraph/s:

A multi-junction type thin-film solar cell of a super-straight type in this Example has substantially the same structure as that shown in Fig. 5. This thin-film solar cell has a substrate for a thin-film solar cell comprising a glass plate and a first transparent conductive layer formed thereon. Formed on this substrate are an amorphous silicon photoelectric conversion layer 27, second transparent conductive layer 11c, crystalline silicon photoelectric conversion layer 37, back surface reflecting layer 15 and back surface electrode 16 in this order. Formed on each surface of the first and second transparent conductive layers are a great number of holes each having approximately a sphere shape and reaching not to the glass plate 11a like the Example 1. The amorphous silicon photoelectric conversion layer 27 is made of a p-type amorphous silicon layer 12a, i-type amorphous silicon layer 13a and n-type amorphous silicon layer 14a, and the crystalline silicon photoelectric conversion layer 37 is made of a p-type crystalline silicon layer 12b, i-type crystalline silicon layer 13b and n-type crystalline silicon layer 14b.

Please replace Table 3 beginning at page 43, line 5, with the following new Table 3:

Table 3

	Etching Time (sec.) Other Forming Condition	Surface Shape of Second Transparent Conductive Layer				I_{220}/I_{111} *
		Hole diameter (nm)	Hole Depth (nm)	Irregularity Size on Hole (nm)	Irregularity Size on other than Hole(nm)	
Ex 6	200	200-1400	80 – 1000	10 – 280 Average 120	<10	3
Ex 7	280	400-1400	100 – 700	20 – 200 Average 150	20 – 40	3
Ex 8	280	400-1400	100 – 700	10 – 200 Average 150	20 – 40	5.5
Ex 9	200 ZnO/ ZnO	200-1400	80 – 1000	20 – 280 Average 130	20 – 50	3
Ex 10	--	400-1000	100 – 700	30 – 120 Average 80	30 – 120	3
Co Ex 4	ZnO/ SnO_2		--	--	Average 100	1.5
Co Ex 5	80	50-200	10 – 100	<10	<10	3
Co Ex 6	200 i- layer** 100nm	200-1400	80 – 1000	10 – 280 Average 120	<10	3
Co Ex 7	200 i- layer** 500nm	200-1400	80 – 1000	10 – 280 Average 100	<10	3
Co Ex 8	--	800-3000	700-2000	150 – 500 Average 350	150 – 500	1.4

* : Orientation of crystalline silicon photoelectric conversion layer
** i-layer : i-type amorphous silicon layer

A3